

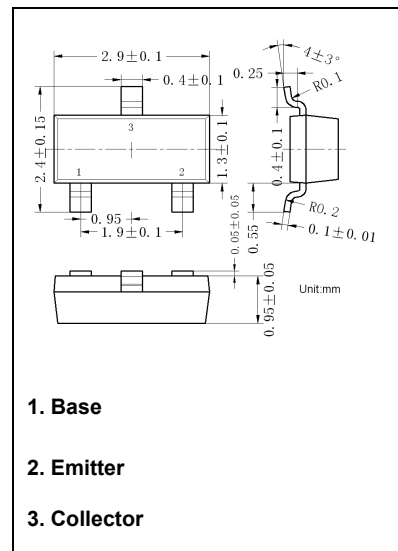
SOT-23 Plastic-Encapsulate Transistors

S9015 TRANSISTOR(PNP)

Features

- Complementary to S9014

Marking: M6



Maximum ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.1	A
P_C	Collector Power Dissipation	0.2	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55 ~ -150	$^{\circ}\text{C}$

Electrical Characteristics ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -100\mu\text{A}$, $I_E = 0$	-50			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -0.1\text{mA}$, $I_B = 0$	-45			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_C = -100\mu\text{A}$, $I_C = 0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB} = -50\text{V}$, $I_E = 0$			-100	nA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5\text{V}$, $I_C = 0$			-100	nA
H_{FE}	DC current gain	$V_{CE} = -5\text{V}$, $I_C = -1\text{mA}$	200		400	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$			-0.3	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$			-1.0	V
f_T	Gain Bandwidth Product	$V_{CE} = -5\text{V}$, $I_C = -10\text{mA}$, $f = 30\text{MHz}$	150			MHz

Typical Characteristics

